

We Claim:

1. A configuration for making contact with a semiconductor substrate, the configuration comprising:

a first sealing ring;

a second sealing ring being larger than said first sealing ring;

a base body having a base-body surface, said first sealing ring and said second sealing ring disposed on said base-body surface, said first sealing ring being disposed completely inside a region of said base-body surface being surrounded by said second sealing ring, said base body having a first opening and a second opening formed therein each starting from said base-body surface and extending between said first sealing ring and said second sealing ring;

a semiconductor substrate having a first main surface and a second main surface, said semiconductor substrate disposed on said first sealing ring and said second sealing ring with said first main surface facing said base body;

a conductive layer having a surface disposed on said semiconductor substrate, said conductive layer disposed such that a current impressed into said conductive layer being

uniformly distributed across said first main surface of said semiconductor substrate;

a first line system connected to said first opening for admitting and discharging at least one electrically conductive liquid;

a second line system connected to said second opening for admitting and discharging the electrically conductive liquid; and

a contact wire disposed uncovered on said base-body surface of said base body between said first sealing ring and said second sealing ring.

2. The configuration according to claim 1, further comprising a first insulating layer disposed on said conductive layer but removed in a region between said first sealing ring and said second sealing ring.

3. The configuration according to claim 2, further comprising an electrolyte source and an etchant source being switchably connected to said first line system.

4. The configuration according to claim 1, wherein said first sealing ring, said second sealing ring, said base-body surface, and said semiconductor substrate delimit a cavity.

5. A method for making contact with a semiconductor substrate, which comprises the following steps:

providing a base body having a base-body surface, a first sealing ring disposed on the base-body surface, and a second sealing ring disposed on the base-body surface, the first sealing ring being smaller than the second sealing ring, the first sealing ring disposed completely inside a region of the base-body surface surrounded by the second sealing ring;

forming a first opening and a second opening in the base body, starting from the base-body surface, between the first sealing ring and the second sealing ring;

disposing a contact wire uncovered on the base-body surface of the base body between the first sealing ring and the second sealing ring;

providing a substrate having a first main surface and a second main surface;

disposing a conductive layer on the first main surface such that a current impressed into the conductive layer being uniformly distributed across the first main surface;

disposing the substrate with the first main surface on the first sealing ring and the second sealing ring so that the first main surface faces the base body, a cavity being formed and delimited by the first sealing ring, the second sealing ring, the base-body surface and the first main surface of the substrate;

introducing an electrolyte through the first opening into the cavity, an electrical connection being formed between the conductive layer and the contact wire; and

discharging the electrolyte through the second opening.

6. The method according to claim 5, which further comprises:

disposing an insulation layer on the conductive layer;

introducing an etching substance, for removing the insulation layer from the conductive layer, into the cavity through the first opening; and

discharging the etching substance from the cavity through the second opening.

7. The method according to claim 5, which further comprises forming a barrier layer, serving as at least one of a diffusion barrier and a bonding agent, between the substrate and the conductive layer.

8. The method according to claim 6, which further comprises forming the insulation layer from a material selected from the group consisting of silicon nitride and silicon oxide; and using an etchant, selected from the group consisting of hydrofluoric acid and nitric acid, for etching the insulation layer and during the etching the conductive layer is uncovered.

9. The method according to claim 6, which further comprises performing a dry-etching process, using an etching mask applied to the substrate, for removing the insulation layer.